

#### Description

The FDD306P uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

V<sub>DS</sub> = 20V I<sub>D</sub> =60 A

 $R_{DS(ON)} < 6m\Omega @ V_{GS}=4.5V$ 

#### Application

Battery protection

Load switch Uninterruptible power supply

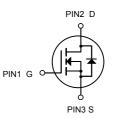
#### Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)	
FDD306P	TO252-2L	60N02 XXX YYYY	2500	

#### Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	20	V
Vgs	Gate-Source Voltage	±12	V
ID	Drain Current-Continuous	60	А
l₀(100℃)	Drain Current-Continuous(Tc=100℃)	42	A
Ом	Pulsed Drain Current	210	A
PD	Maximum Power Dissipation	60	W
	Derating factor	0.48	W/℃
Eas	Single pulse avalanche energy (Note 5)	200	mJ
Тј,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Rejc	Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	2.1	°C <b>/W</b>





N-Channel MOSFET



## Electrical Characteristics (Tc=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	20	-	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V,V <sub>GS</sub> =0V	-			μA
Gate-Body Leakage Current	lgss	V <sub>GS</sub> =±12V,V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA	0.5	0.75	1.0	V
	_	V <sub>GS</sub> =4.5V, I <sub>D</sub> =20 A -		4.5	6	mΩ
Drain-Source On-State Resistance	V <sub>GS</sub> =2.5V, I <sub>D</sub> =15A			5.3	8.2	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =10V,I <sub>D</sub> =20A	15	-	-	S
Input Capacitance	C <sub>lss</sub>		-	2000	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =10V,V <sub>GS</sub> =0V,	-	500	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	200	-	PF
Turn-on Delay Time	td(on)		-	6.4	-	nS
Turn-on Rise Time	tr		-	17.2	-	nS
Turn-Off Delay Time	td(off)	$V_{GS}$ =4.5V, $R_{G}$ =3 $\Omega$	-	29.6	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	16.8	-	nS
Total Gate Charge	Qg		-	27		nC
Gate-Source Charge	Qgs	V <sub>DS</sub> =10V,I <sub>D</sub> =20A,	-	6.5		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	6.4		nC
Diode Forward Voltage (Note 3)	Vsd	V <sub>GS</sub> =0V,I <sub>S</sub> =10A	-		1.2	V
Diode Forward Current (Note 2)	ls		-	-	60	Α
Reverse Recovery Time	t <sub>rr</sub>	TJ = 25°C, IF = 20A	-	25	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs <sup>(Note3)</sup>	-	24	-	nC
Forward Turn-On Time	ton	Intrinsic turn-on time is neg LS+LD)	ligible (turn-on is dominated by			

#### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

**2.** Surface Mounted on FR4 Board,  $t \le 10$  sec.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production

**5.** E<sub>AS</sub> condition : Tj=25 $^{\circ}$ C,V<sub>DD</sub>=10V,V<sub>G</sub>=10V,L=0.5mH,Rg=25 $\Omega$ ,



25

12

0.6

0.8

18

24

T<sub>J</sub> = 25 °C

1.0

1.2

30

50

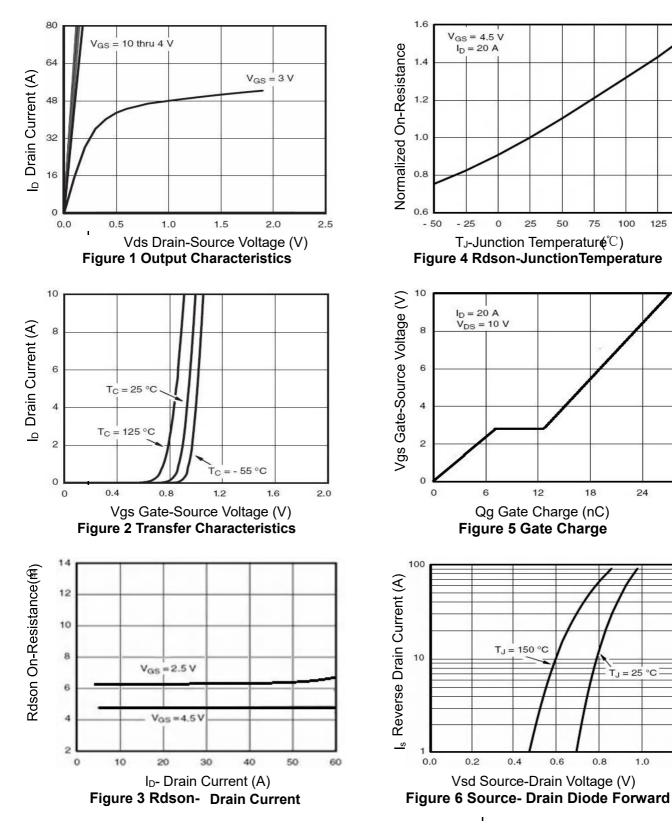
75

100

125

150

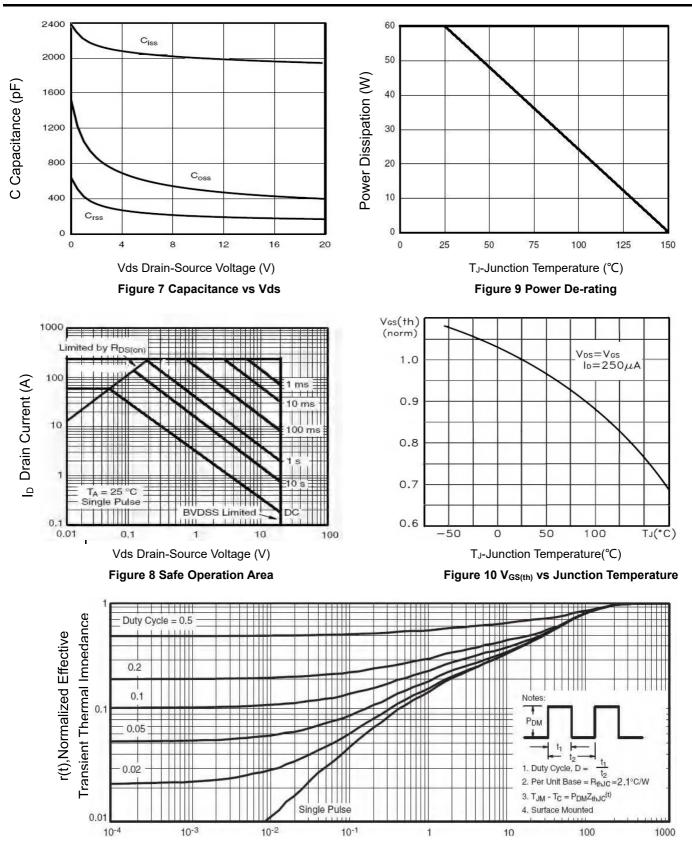
#### **Typical Electrical and Thermal Characteristics (Curves)**



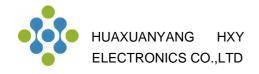


# FDD306P

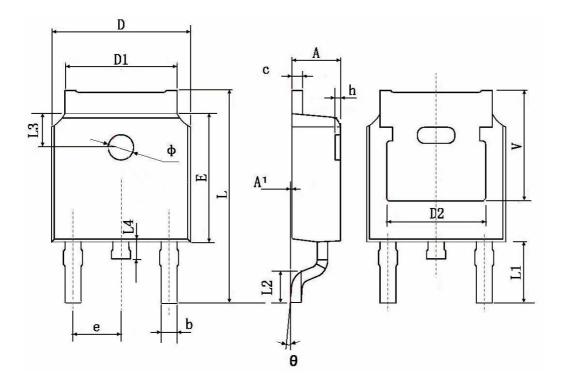
N-Channel Enhancement Mode MOSFET



Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance



# TO252-2L Package Information



	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
с	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	0.483	TYP.	0.190	) TYP.	
E	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114	TYP.	
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063	B TYP.	
L4	0.600	1.000	0.024	0.039	
Φ	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350	TYP.	0.211 TYP.		



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